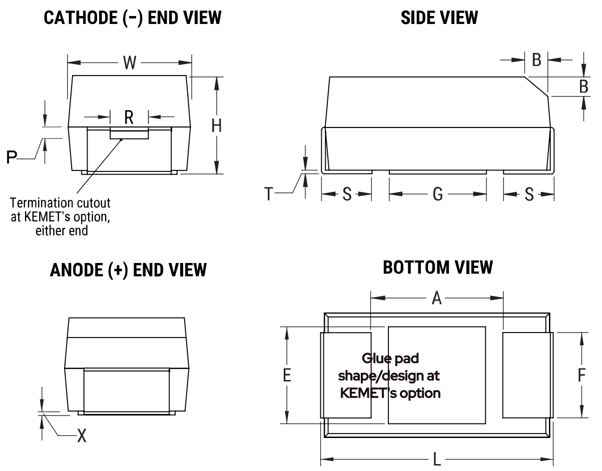
T496D475M050ATE400

T496, Tantalum, MnO2 Tantalum, Fused, 4.7 uF, 20%, 50 VDC, SMD, MnO2, Molded, Fused, N/A, 400 mOhms, 7343, 3.1 mm, 1.3 mm



Click here for the 3D model.

General Information

General Information	
Series	T496
Dielectric	MnO2 Tantalum
Style	SMD Chip
Description	SMD, MnO2, Molded, Fused
Features	Integral Fuse
RoHS	Yes
Termination	Tin
AEC-Q200	No
Typical Component Weight	446.84 mg
Shelf Life	156 Weeks
MSL	1

Dimensions

Dimensions	
L	7.3mm +/-0.3mm
W	4.3mm +/-0.3mm
H	2.8mm +/-0.3mm
T	0.13mm REF
S	1.3mm +/-0.3mm
F	2.4mm +/-0.1mm
A	3.8mm MIN
B	0.5mm +/-0.15mm
E	3.5mm REF
G	3.5mm REF
P	0.9mm REF
R	1mm REF
X	0.1mm +/-0.1mm REF

Specifications

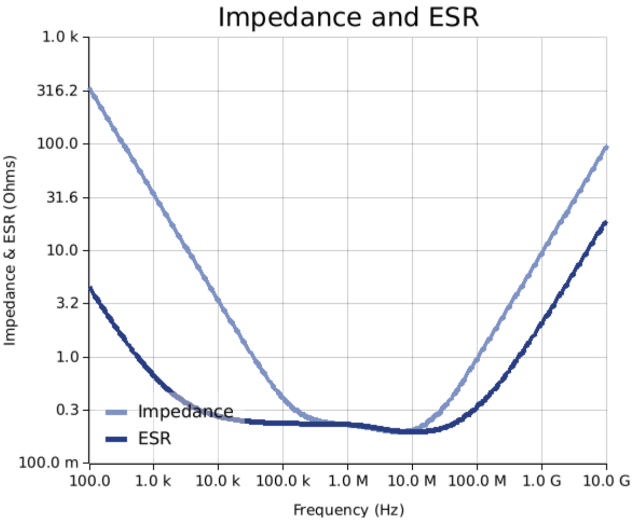
Specifications	
Capacitance	4.7 uF
Tolerance	20%
Voltage DC	50 VDC (85C), 33.5 VDC (125C)
Temperature Range	-55/+125°C
Rated Temperature	85°C
Dissipation Factor	6% 120Hz 25C
Failure Rate	N/A
ESR	400 mOhms (100kHz 25C)
Ripple Current	612 mA (rms, 100kHz 25C), 550.8 mA (rms, 85C), 244.8 mA (rms, 125C)
Leakage Current	2.4 uA (5min 25°C)

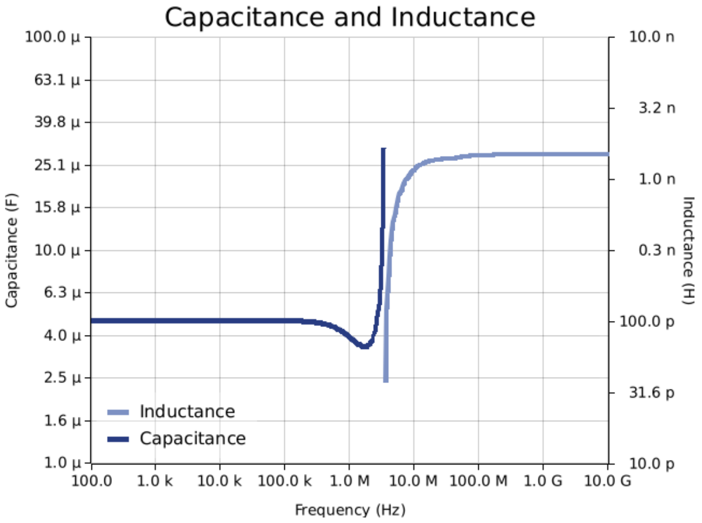
Packaging Specifications

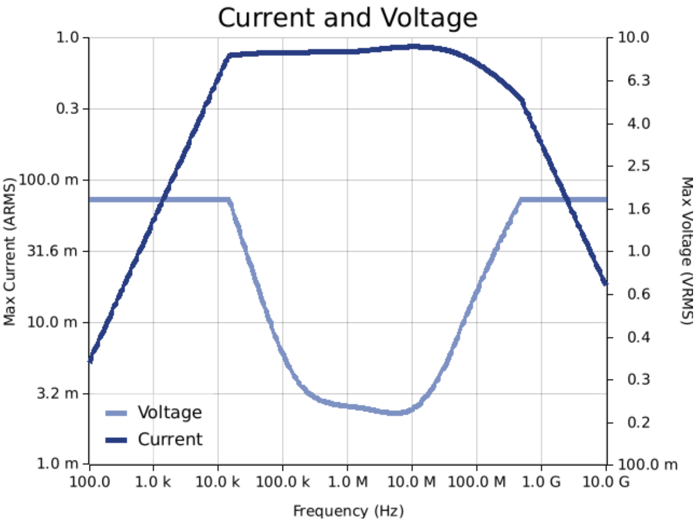
Packaging Specifications	
Packaging	T&R, 178mm
Packaging Quantity	500

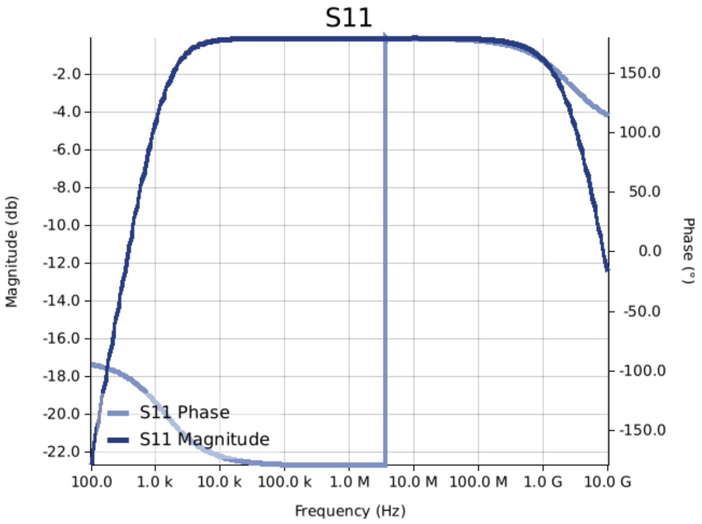
Simulations

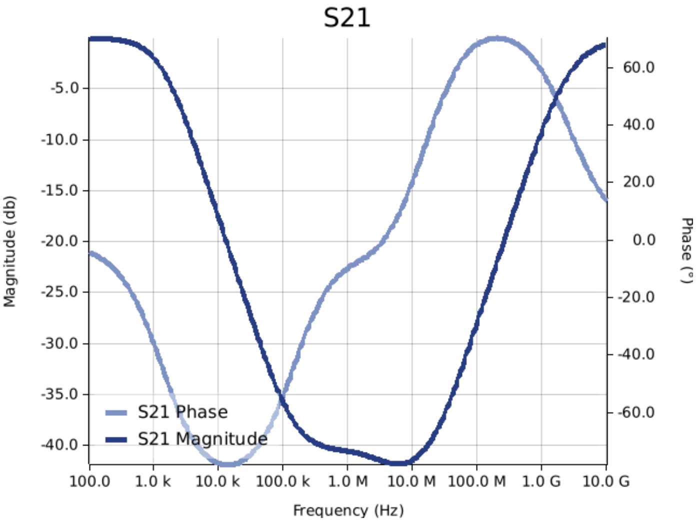
For the complete simulation environment please visit K-SIM.











These are simulations.
This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple “Ripple Current/Voltage vs. Frequency” plots is the ESR at ambient temperature.
- The ESR in the “Temperature Rise vs. Ripple Current” plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
- The effects shown herein are based on measured data from a multiple part sample of the parts in question.
- Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.
- The peak voltages generated in the “Temperature Rise vs. Combined Ripple Currents” plot are calculated for each frequency and are not combined with voltages generated at any other harmonics.
- Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the “Information”) are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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